Thin Solid Films, *221* (1992) 324–325

Author Index of Volume 221

Abe, Y., 220
Adamec, F., 281
Agrawal, A., 239
Agrawal, R. K., 239
Al-Robaee, M. S., 214
Albrecht, O., 276
Ambroz, M., 281
Andrzejak, C., 27
Artunç, N., 207
Asai, N., 285
Aymerich, X., 147

Balog, P., 281
Beldon, H. S., 262
Berger, M. G., 27
Bhattacharyya, D., 154
Boakye, F., 224
Bozack, M. J., 55
Brückner, W., 140
Bruyère, J. C., 65
Brynda, E., 281
Bulhões, L. O. S., 5

Cai, Y., 271
Caron-Popowich, R'S., 239
Chaudhuri, S., 154
Cho, H.-C., 203
Choi, J.-S., 203
Chou, T. C., 89
Chung, W.-Y., 304
Clement, M., 21
Coath, J. A., 262
Cronin, J. P., 239

Delgado, J. C., 17
Dian, J., 281

Efimov, V. M., 160
Eguchi, K., 276
Ehrhardt, J. J., 114
Esaev, D. G., 160

Faria, R. M., 5
Fen, X. B., 34
Feng, Z. R., 9
Ferreira, M., 5
Fujiwara, I., 285
Fuyama, M., 20

Gadenne, M., 183
Gadenne, P., 183
Gao, Q. J., 34
Gonçalves, D., 5
Granko, V. I., 191
Grassie, A. D. C., 224
Grießmann, H., 140
Gromovoj, Yu. S., 127
Gupta, P., 154

Habibi, H. R., 239
Hala, J., 281
Hasmonay, H., 292
Heinrich, A., 140
Herino, R., 27
Hiraoka, K., 120
Hochapfel, A., 292
Holloway, P. H., 254
Howarth, V., 285
Hua, Z., 271
Huang, N. K., 9
Hunnikin, B. J., 262
Hwang, Y.-S., 203

Ionov, R., 39
Ishii, H., 98
Itabashi, S., 79

Jaffrain, M., 292
Jiang, G. S., 34
Joswig, H., 228
Joubert, J. C., 44

Klad'ko, V. P., 127
Klemradt, U., 27
Kobayashi, K., 298
Kostyunin, G. E., 127
Krasnitsky, V. Y., 191
Kravtsov, S. V., 191
Krüeger, D., 61
Kukushkin, S. A., 267
Kurps, R., 61

Lampert, C. M., 23
Lane, D. W., 262
Langlet, M., 44
Lazzari, J. L., 196
Lee, D.-D., 304
Lesnikova, V. P., 191
Li, J. H., 34
Ligeon, M., 27
Lin, Z. D., 34
Lippert, G., 61
Liu, R., 318
Llinares, C., 196
Lu, F. X., 34
Lu, M., 271
Luo, W., 271
Lüth, H., 27

Marage, P., 44
Martín, F., 147
Martin, J. C., 183
Martínez-Duart, J. M., 21
Matsuda, H., 276
Mattoso, L. H. C., 5
Mayer, B., 166
Meletis, E. I., 104
Mezerreg, A., 196
Mohan, S., 214
Mönch, J.-I., 140
Montaner, A., 196
Mueller, C. H., 254
Münder, H., 27
Muraleedharan, T. M., 104
Murunaka, S., 1

Nakagiri, T., 276
Nakayama, T., 220
Nalivaiko, O. Y., 191
Narashimha Rao, K., 214
Nieh, T. G., 89
Nishiguchi, K., 98
Nishikawa, K., 72
Nosaka, T., 72

Ogawa, S., 72
Okamoto, A., 72
Oliveira, Jr., O. N., 5
Onisawa, K., 220
Ono, Y. A., 220
Osten, H. J., 61
Öztürk, Z. Z., 207

Paek, S.-H., 203
Pal, A. K., 154
Pamler, W., 228
Pelleg, J., 318
Pen, X. F., 34
Peretti, P., 292
Plyatsko, S. V., 127

Reynes, B., 65
Roberts, D. M., 239
Roch, C., 17, 65
Roeser, D., 61
Rogers, K. D., 262
Rubets, V. P., 267

Sambles, J. R., 311
Sanz, J. M., 21
Sarychev, O. E., 191
Savall, C., 65
Schubert, G., 140
Sebastian, P. J., 233
Sella, C., 183
Selvi, S., 207
Shen, X., 271
Shivalingappa, L., 214
Shklyaev, A. A., 160
Silvain, J. F., 114
Sisk, P. J., 13
Sizov, F. F., 127
Smal, I. V., 191
Sohn, B.-K., 304
Sundaram, K. B., 13

Tajima, K., 298
Takahashi, K., 98
Takahashi, M., 298
Takahashi, Y., 98

Tamaoki, N., 132
Turtsevich, A. S., 191

Vacha, M., 281
Veyrat, A., 114
Vukusic, P. S., 311

Wahid, P. F., 13
Walz, D., 44
Wang, D. Z., 9

Yamaoka, T., 132
Yang, B. X., 34
Yang, N., 271
Yang, Y. C., 34
Yoshihara, H., 79
Yoshimura, S., 132
Yoshitake, M., 72
Yuan, H., 34

Zeng, Y., 271
Zhang, X., 34
Zhang, Z., 271

Subject Index of Volume 221

Acetylene
  deposition of Zr–C thin films and plasma-polymerized hydrocarbon films in the reactive magnetron sputtering process, 72
Adhesion
  effect of the temperature on the adhesion and the morphology of thin metal films evaporated on polyethlene terephthalate, 114
Adsorption
  adsorbability of dye molecules on Langmuir–Blodgett films of long-chain alkylammonium salts, 298
Aluminium
  change in the stress of aluminium thin films during high temperature storage, 120
Aluminium oxide
  interface-controlled phase transformation and abnormal grain growth of α-Al_2O_3 in thin γ-alumina films, 89
Amorphous materials
  correlation between hydrogen thermal evolution and morphology in glow discharge deposited a-Si:H films, 17
  high temperature stability of CrSi(W)–N films, 140
Anisotropy
  adsorbability of dye molecules on Langmuir–Blodgett films of long-chain alkylammonium salts, 298
  control of the homogeneity of Langmuir–Blodgett films using the deposition-induced flow in the monolayer, 276
Annealing
  annealing of silicon nitride thin films prepared by plasma-enhanced chemical vapour deposition with helium dilution, 65
Auger electron spectroscopy
  changes induced in the room temperature oxidation of $TiSi_x$ by Ar^+ bombardment, 21
  reaction of tungsten hexafluoride with Si and TiN surfaces, 55
  stoichiometry effects in TiN diffusion barriers, 228
  role of the silver intermediate layer in $YBa_2Cu_3O_{7-x}/Ag/In_2O_3/Si$ system, 271
  valance Auger analysis of the annealing effect on atomic interaction at titanium–sapphire, titanium–silica and silver–silica interfaces, 98

Biomaterials
  monolayer study of the antibiotic ionophore monensin: pH influence and salt effects, 292

Cadmium telluride
  electrical properties of vacuum-evaporated stoichiometric and non-stoichiometric CdTe thin films for opto-electronic applications, 233
Carbides
  deposition of Zr–C thin films and plasma polymerized hydrocarbon films in the reactive magnetron sputtering process, 72
Chemical vapour deposition
  study of interface structure between diamond films and silicon substrate, 34
  growth kinetics of low pressure chemically vapour deposited selective tungsten films in WF_6–Si and WF_6–H_2 systems, 191
  highly conductive and transparent films of tin and fluorine doped indium oxide produced by APCVD, 166
Chemisorption
  electrical properties of vacuum-evaporated stoichiometric and non-stoichiometric CdTe thin films for opto-electronic applications, 233
Coatings
  effect of deposition pressure on the microstructure and electrochromic properties of electron-beam-evaporated nickel oxide films, 239
  surface modification of pure titanium and Ti–6Al–4V by intensified plasma ion nitriding, 104
Copper
  effects of surface and interface scattering on the electrical resistivity of Cu/Ag double-layered thin films, 207
Corrosion
  surface modification of pure titanium and Ti–6Al–4V by intensified plasma ion nitriding, 104

Deposition process
  control of the homogeneity of Langmuir–Blodgett films using the deposition-induced flow in the monolayer, 276
  glass and ceramic thin films deposited by an ultrasonically assisted sol–gel technique, 44
  reaction of tungsten hexafluoride with Si and TiN surfaces, 55
Diamond
  study of interface structure between diamond film and silicon substrate, 34
Dielectric properties
  dielectric breakdown properties of Ta_2O_5/SiO_2 stacked thin films prepared by r.f. sputtering, 220
Diffusion
  stoichiometry effects in TiN diffusion barriers, 228
  surface modification of pure titanium and Ti–6Al–4V by intensified plasma ion nitriding, 104

Electrical properties and measurements
  composition and electrical properties of $Au–Al_2O_3$ cermet thin films: a critical study, 183
  determination of electrical and optical parameters of $Ga_{1-x}In_xAs_ySb_{1-y}$ and $Ga_{1-x}Al_xAs_ySb_{1-y}$ thin layers grown on GaSb substrates by IR reflectivity, 196
  high temperature stability of CrSi(W)–N films, 140
  highly conductive and transparent films of tin and fluorine doped indium oxide produced by APCVD, 166
  preparation and characterization of polycrystalline ZnS_xSe_{1-x} films prepared by a two-zone hot wall technique, 154
Electrochemistry
  effect of deposition pressure on the microstructure and electrochromic properties of electron-beam-evaporated nickel oxide films, 239
Electron diffraction
  study of interface structure between diamond film and silicon substrate, 34
Evaporation
  laser-assisted evaporation of high-quality narrow-gap thin films, 127

Field emission microscopy
  field emission and field ion microscopy of zirconiated tungsten emitter, 318

Field ion microscopy
field emission and field ion microscopy of zirconiated tungsten emitter, 318
Fluorescence
role of central metal in phthalocyanine Langmuir–Blodgett films studied by hole burning, 281

Gallium
chemical reactions at metal/compound semiconductor interfaces: Au and GaAs, 254
Grain boundary
change in the stress of aluminium thin films during high temperature storage, 120
preparation and characterization of polycrystalline ZnS_xSe_{1-x} films prepared by a two-zone hot wall technique, 154
Growth mechanism
characterization of surfactant introduction into germanium-rich $Si_{1-x}Ge_x$ molelcular beam epitaxy layer growth on silicon by means of secondary-ion mass spectrometry and Auger electron spectroscopy, 61
growth kinetics of low pressure chemically vapour deposited selective tungsten films in WF_6–Si and WF_6–H_2 systems, 191
interface-controlled phase transformation and abnormal grain growth of α-Al_2O_3 in thin γ-alumina films, 89

Hydrocarbons
effects of added TiO_2 on characteristics of SnO_2-based thick film gas sensors, 304
Hydrogen
annealing of silicon nitride thin films prepared by plasma-enhanced chemical vapour deposition with helium dilution, 65
correlation between hydrogen thermal evolution and morphology in glow discharge deposited a-Si:H films, 17
effect of hydrogen on hot electron energy relaxation in SiO_2 and Si_3N_4 films, 160

Indium oxide
highly conductive and transparent films of tin and fluorine doped indium oxide produced by APCVD, 166
Infrared spectroscopy
annealing of silicon nitride thin films prepared by plasma-enhanced chemical vapour deposition with helium dilution, 65
determination of electrical and optical parameters of $Ga_{1-x}In_xAs_ySb_{1-y}$ and $Ga_{1-x}Al_xAs_ySb_{1-y}$ thin layers grown on GaSb substrates by IR reflectivity, 196
Interface
study of interface structure between diamond film and silicon substrate, 34
interface-controlled phase transformation and abnormal grain growth of α-Al_2O_3 in thin γ-alumina films, 89
interface-induced structural changes in amorphous chalcogenide superlattices, 39
valence Auger analysis of the annealing effect on atomic interaction at titanium–sapphire, titanium–silica and silver–silica interfaces, 98
Ion bombardment
changes induced in the room temperature oxidation of $TiSi_x$ by Ar^+ bombardment, 21
influence of substrate temperature on the properties of argon-ion-assisted-deposited CeO_2 films, 214
microanalyses of Ar^+-bombarded zirconia–yttria films on silicon substrates, 9

Langmuir–Blodgett films
adsorbability of dye molecules on Langmuir–Blodgett films of long-chain alkylammonium salts, 298
control of the homogeneity of Langmuir–Blodgett films using the deposition-induced flow in the monolayer, 276
preparation and characterization of a novel Langmuir–Blodgett film optical waveguide with non-linear optical susceptibility inversion, 285
role of central metal in phthalocyanine Langmuir–Blodgett films studied by hole burning, 281
Liquid phase epitaxy
determination of electrical and optical parameters of $Ga_{1-x}In_xAs_ySb_{1-y}$ and $Ga_{1-x}Al_xAs_ySb_{1-y}$ thin layers grown on GaSb substrates by IR reflectivity, 196

Manganese
influence of deposition parameters on the low temperature resistivity of α-Mn thin films, 224
Metallization
change in the stress of aluminium thin films during high temperature storage, 120
reaction of tungsten hexafluoride with Si and TiN surfaces, 55
stoichiometry effects in TiN diffusion barriers, 228
valence Auger analysis of the annealing effect on atomic interaction at titanium–sapphire, titanium–silica and silver–silica interfaces, 98
Metals
characterization of the spatial distribution of traps in Si_3N_4 by field-assisted discharge of metal–nitride–oxide–semiconductor devices, 147
effect of the temperature on the adhesion and the morphology of thin metal films evaporated on polyethylene terephthalate, 114
Migration mechanisms
determination of migration mechanisms and their influence on the structure of films, 267
Molecular beam epitaxy
characterization of surfactant introduction into germanium-rich $Si_{1-x}Ge_x$ molecular beam epitaxy layer growth on silicon by means of secondary-ion mass spectrometry and Auger electron spectroscopy, 61
Monolayers
monolayer study of the antibiotic ionophore monensin: pH influence and salt effects, 292
adsorbability of dye molecules on Langmuir–Blodgett films of long-chain alkylammonium salts, 298
Multilayers
control of the homogeneity of Langmuir–Blodgett films using the deposition-induced flow in the monolayer, 276

Nanostructures
detailed Raman study of porous silicon, 27
composition and electrical properties of Au–Al_2O_3 cermet thin films: a critical study, 183
preparation and characterization of a novel Langmuir–Blodgett film optical waveguide with non-linear optical susceptibility inversion, 285
Nickel oxide
effect of deposition pressure on the microstructure and electrochromic properties of electron-beam-evaporated nickel oxide films, 239
Nitrogen dioxide
cobalt phthalocyanine as a basis for the optical sensing of nitrogen dioxide using surface plasmon resonance, 311

Optical coatings
composition and electrical properties of $Au-Al_2O_3$ cermet thin films: a critical study, 183
influence of substrate temperature on the properties of argon-ion-assisted-deposited CeO_2 films, 214
Optical properties
photochromic memory with a non-destructive read-out property, 132
characterization and optimization of cerium dioxide films deposited by r.f. magnetron sputtering, 13
determination of electrical and optical parameters of $Ga_{1-x}In_xAs_ySb_{1-y}$ and $Ga_{1-x}Al_xAs_ySb_{1-y}$ thin layers grown on GaSb substrates by IR reflectivity, 196
highly conductive and transparent films of tin and fluorine doped indium oxide produced by APCVD, 166
influence of substrate temperature on the properties of argon-ion-assisted-deposited CeO_2 films, 214
optical properties and structure of thermally evaporated tin oxide films, 262
preparation and characterization of a novel Langmuir–Blodgett film optical waveguide with non-linear optical susceptibility inversion, 285
Optical spectroscopy
photochromic memory with a non-destructive read-out property, 132
Organic substances
photochromic memory with a non-destructive read-out property, 132
Oxidation
changes induced in the room temperature oxidation of $TiSi_x$ by Ar^+ bombardment, 21
Oxides
characterization and optimization of cerium dioxide films deposited by r.f. magnetron sputtering, 13
Oxygen
electrical properties of vacuum-evaporated stoichiometric and non-stoichiometric CdTe thin films for opto-electronic applications, 233

Physical vapour deposition
characterization and optimization of cerium dioxide films deposited by r.f. magnetron sputtering, 13
high temperature stability of CrSi(W)–N films, 140
Platinum
surface evaluation of ultrathin platinum films, 79
Polyethylene terephthalate
effect of the temperature on the adhesion and the morphology of thin metal films evaporated on polyethylene terephthalate, 114
Polymers
photochromic memory with a non-destructive read-out property, 132

Raman scattering
detailed Raman study of porous silicon, 27
preparation and characterization of polycrystalline ZnS_xSe_{1-x} films prepared by a two-zone hot wall technique, 154
Reaction kinetics
valence Auger analysis of the annealing effect on atomic interaction at titanium–sapphire, titanium–silica and silver–silica interfaces, 98
Resistivity
influence of deposition parameters on the low temperature resistivity of α-Mn thin films, 224
Rutherford backscattering spectroscopy
optical properties and structure of thermally evaporated tin oxide films, 262

Scattering
effects of surface and interface scattering on the electrical resistivity of Cu/Ag double-layered thin films, 207
Second harmonic generation
preparation and characterization of a novel Langmuir–Blodgett film optical waveguide with non-linear optical susceptibility inversion, 285
Secondary ion mass spectrometry
characterization of surfactant introduction into germanium-rich $Si_{1-x}Ge_x$ molelcular beam epitaxy layer growth on silicon by means of secondary-ion mass spectrometry and Auger electron spectroscopy, 61
Selenium
interface-induced structural changes in amorphous chalcogenide superlattices, 39
Semiconductor
characterization of the spatial distribution of traps in Si_3N_4 by field-assisted discharge of metal–nitride–oxide–semiconductor devices, 147
Semiconductors
determination of migration mechanisms and their influence on the structure of films, 267
electrical characteristics of $TaSi_2-P^+$-Si and $TiSi_2-P^+$-Si contacts formed by rapid thermal annealing, 203
preparation and characterization of polycrystalline ZnS_xSe_{1-x} films prepared by a two-zone hot wall technique, 154
Sensors
cobalt phthalocyanine as a basis for the optical sensing of nitrogen dioxide using surface plasmon resonance, 311
effects of added TiO_2 on characteristics of SnO_2-based thick film gas sensors, 304
Silicides
changes induced in the room temperature oxidation of $TiSi_x$ by Ar^+ bombardment, 21
electrical characteristics of $TaSi_2-P^+$-Si and $TiSi_2-P^+$-Si contacts formed by rapid thermal annealing, 203
Silicon
detailed Raman study of porous silicon, 27
Silicon nitride
annealing of silicon nitride thin films prepared by plasma-enhanced chemical vapour deposition with helium dilution, 65
characterization of the spatial distribution of traps in Si_3N_4 by field-assisted discharge of metal–nitride–oxide–semiconductor devices, 147
effect of hydrogen on hot electron energy relaxation in SiO_2 and Si_3N_4 films, 160
Silicon oxide
dielectric breakdown properties of Ta_2O_5/SiO_2 stacked thin films prepared by r.f. sputtering, 220
effect of hydrogen on hot electron energy relaxation in SiO_2 and Si_3N_4 films, 160
glass and ceramic thin films deposited by an ultrasonically assisted sol–gel technique, 44
Silver
chemical reactions at metal/compound semiconductor interfaces: Au and GaAs, 254
effects of surface and interface scattering on the electrical resistivity of Cu/Ag double-layered thin films, 207

Sputtering
deposition of Zr–C thin films and plasma-polymerized hydrocarbon films in the reactive magnetron sputtering process, 72
dielectric breakdown properties of Ta_2O_5/SiO_2 stacked thin films prepared by r.f. sputtering, 220
role of the silver intermediate layer in $YBa_2Cu_3O_{7-x}/Ag/In_2O_3/Si$ system, 271
Stress
change in the stress of aluminium thin films during high temperature storage, 120
high temperature stability of CrSi(W)–N films, 140
Structural properties
influence of substrate temperature on the properties of argon-ion-assisted-deposited CeO_2 films, 214
Structure
determination of migration mechanisms and their influence on the structure of films, 267
Superconductivity
role of the silver intermediate layer in $YBa_2Cu_3O_{7-x}/Ag/In_2O_3/Si$ system, 271
Superlattices
interface-induced structural changes in amorphous chalcogenide superlattices, 39
Surface and interface states
monolayer study of the antibiotic ionophore monensin: pH influence and salt effects, 292
Surface energy
interface-controlled phase transformation and abnormal grain growth of α-Al_2O_3 in thin γ-alumina films, 89
Surface morphology
correlation between hydrogen thermal evolution and morphology in glow discharge deposited a-Si:H films, 17
effect of deposition pressure on the microstructure and electrochromic properties of electron-beam-evaporated nickel oxide films, 239
surface evaluation of ultrathin platinum films, 79
Surface plasmons
cobalt phthalocyanine as a basis for the optical sensing of nitrogen dioxide using surface plasmon resonance, 311
Surface pressure
monolayer study of the antibiotic ionophore monensin: pH influence and salt effects, 292
Surface roughness
surface evaluation of ultrathin platinum films, 79
Surface segregation
characterization of surfactant introduction into germanium-rich $Si_{1-x}Ge_x$ molelcular beam epitaxy layer growth on silicon by means of secondary-ion mass spectrometry and Auger electron spectroscopy, 61
Tantalum
dielectric breakdown properties of Ta_2O_5/SiO_2 stacked thin films prepared by r.f. sputtering, 220
electrical characteristics of $TaSi_2$–P^+-Si and $TiSi_2$–P^+-Si contacts formed by rapid thermal annealing, 203
Thermal desorption
correlation between hydrogen thermal evolution and morphology in glow discharge deposited a-Si:H films, 17
Tin oxide
effects of added TiO_2 on characteristics of SnO_2-based thick film gas sensors, 304
optical properties and structure of thermally evaporated tin oxide films, 262
Titanium
electrical characteristics of $TaSi_2$–P^+-Si and $TiSi_2$–P^+-Si contacts formed by rapid thermal annealing, 203
Titanium nitride
stoichiometry effects in TiN diffusion barriers, 228
surface modification of pure titanium and Ti–6Al–4V by intensified plasma ion nitriding, 104
Titanium oxide
effects of added TiO_2 on characteristics of SnO_2-based thick film gas sensors, 304
glass and ceramic thin films deposited by an ultrasonically assisted sol–gel technique, 44
Tungsten
field emission and field ion microscopy of zirconiated tungsten emitter, 318
growth kinetics of low pressure chemically vapour deposited selective tungsten films in WF_6–Si and WF_6–H_2 systems, 191
reaction of tungsten hexafluoride with Si and TiN surfaces, 55

Vacancies
electrical properties of vacuum-evaporated stoichiometric and non-stoichiometric CdTe thin films for opto-electronic applications, 233

X-ray diffraction
detailed Raman study of porous silicon, 27
optical properties and structure of thermally evaporated tin oxide films, 262
role of the silver intermediate layer in $YBa_2Cu_3O_{7-x}/Ag/In_2O_3/Si$ system, 271
X-ray total reflection analysis
surface evaluation of ultrathin platinum films, 79

Zirconium
deposition of Zr–C thin films and plasma polymerized hydrocarbon films in the reactive magnetron sputtering process, 72
field emission and field ion microscopy of zirconiated tungsten emitter, 318